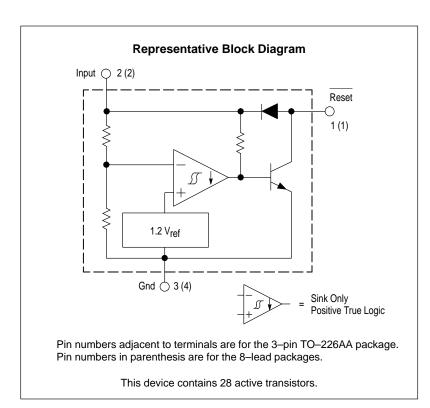


Micropower Undervoltage Sensing Circuits

The MC34164 series are undervoltage sensing circuits specifically designed for use as reset controllers in portable microprocessor based systems where extended battery life is required. These devices offer the designer an economical solution for low voltage detection with a single external resistor. The MC34164 series features a bandgap reference, a comparator with precise thresholds and built–in hysteresis to prevent erratic reset operation, an open collector reset output capable of sinking in excess of 6.0 mA, and guaranteed operation down to 1.0 V input with extremely low standby current. These devices are packaged in 3–pin TO–226AA, 8–pin SO–8 and Micro–8 surface mount packages.

Applications include direct monitoring of the 3.0 or 5.0 V MPU/logic power supply used in appliance, automotive, consumer, and industrial equipment.

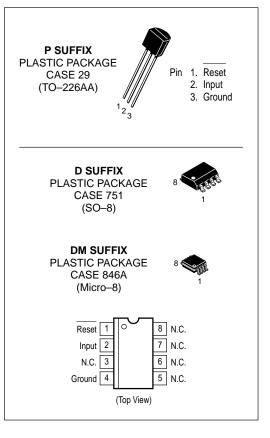
- Temperature Compensated Reference
- Monitors 3.0 V (MC34164-3) or 5.0 V (MC34164-5) Power Supplies
- Precise Comparator Thresholds Guaranteed Over Temperature
- Comparator Hysteresis Prevents Erratic Reset
- Reset Output Capable of Sinking in Excess of 6.0 mA
- Internal Clamp Diode for Discharging Delay Capacitor
- Guaranteed Reset Operation With 1.0 V Input
- Extremely Low Standby Current: As Low as 9.0 μA
- Economical TO-226AA, SO-8 and Micro-8 Surface Mount Packages



MC34164 MC33164

MICROPOWER UNDERVOLTAGE SENSING CIRCUITS

SEMICONDUCTOR TECHNICAL DATA



ORDERING INFORMATION

Device	Operating Temperature Range	Package
MC34164D-3		SO-8
MC34164D-5		30-6
MC34164DM-3	T 0° to 170°C	Missis
MC34164DM-5	$T_A = 0^\circ \text{ to } +70^\circ C$	Micro-8
MC34164P-3		TO 00044
MC34164P-5		TO-226AA
MC33164D-3		SO-8
MC33164D-5		30-6
MC33164DM-3	$T_A = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	
MC33164DM-5		Micro-8
MC33164P-3		TO 00044
MC33164P-5		TO-226AA

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Input Supply Voltage	V _{in}	-1.0 to 12	V
Reset Output Voltage	V _O	-1.0 to 12	V
Reset Output Sink Current	l _{Sink}	Internally Limited	mA
Clamp Diode Forward Current, Pin 1 to 2 (Note 1)	lF	100	mA
Power Dissipation and Thermal Characteristics P Suffix, Plastic Package			
Maximum Power Dissipation @ T _A = 25°C	PD	700	mW
Thermal Resistance, Junction-to-Air	$R_{\theta JA}$	178	°C/W
D Suffix, Plastic Package			
Maximum Power Dissipation @ T _A = 25°C	PD	700	mW
Thermal Resistance, Junction-to-Air DM Suffix, Plastic Package	$R_{\theta JA}$	178	°C/W
Maximum Power Dissipation @ T _A = 25°C	PD	520	mW
Thermal Resistance, Junction-to-Air	$R_{\theta JA}$	240	°C/W
Operating Junction Temperature	TJ	+150	°C
Operating Ambient Temperature Range	TA		°C
MC34164 Series		0 to +70	
MC33164 Series		- 40 to + 85	
Storage Temperature Range	T _{stg}	- 65 to +150	°C

NOTE: ESD data available upon request.

MC34164-3, MC33164-3 SERIES

ELECTRICAL CHARACTERISTICS (For typical values $T_A = 25$ °C, for min/max values T_A is the operating ambient temperature range that applies [Notes 2 & 3], unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
COMPARATOR					
Threshold Voltage High State Output (V _{in} Increasing) Low State Output (V _{in} Decreasing) Hysteresis (I _{Sink} = 100 μA)	VIH VIL VH	2.55 2.55 0.03	2.71 2.65 0.06	2.80 2.80 –	V
RESET OUTPUT	•	•		•	
Output Sink Saturation $(V_{in} = 2.4 \text{ V}, I_{Sink} = 1.0 \text{ mA})$ $(V_{in} = 1.0 \text{ V}, I_{Sink} = 0.25 \text{ mA})$	VoL	- -	0.14 0.1	0.4 0.3	V
Output Sink Current (V _{in} , Reset = 2.4 V)	l _{Sink}	6.0	12	30	mA
Output Off-State Leakage (V _{in} , Reset = 3.0 V) (V _{in} , Reset = 10 V)	IR(leak)	- -	0.02 0.02	0.5 1.0	μА
Clamp Diode Forward Voltage, Pin 1 to 2 (I _F = 5.0 mA)	VF	6.0	0.9	1.2	V
TOTAL DEVICE	•	•		•	ı
Operating Input Voltage Range	V _{in}	1.0 to 10	-	-	V
Quiescent Input Current Vin = 3.0 V Vin = 6.0 V	lin	- -	9.0 24	15 40	μА

NOTES: 1. Maximum package power dissipation limits must be observed.

2. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.

3. T_{low} = 0°C for MC34164

- 40°C for MC33164

Thigh = +70°C for MC34164

= +85°C for MC33164

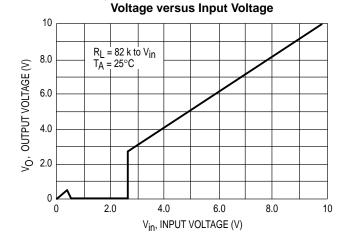
MC34164-5, MC33164-5 SERIES

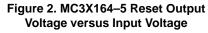
 $\textbf{ELECTRICAL CHARACTERISTICS} \ (\text{For typical values T}_{A} = 25^{\circ}\text{C}, \text{ for min/max values T}_{A} \text{ is the operating ambient temperature range} \\$ that applies [Notes 2 & 3], unless otherwise noted.)

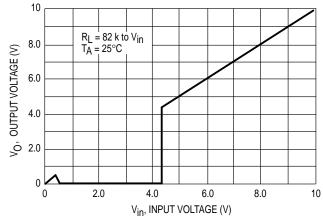
Characteristic	Symbol	Min	Тур	Max	Unit
COMPARATOR	<u>.</u>				
Threshold Voltage High State Output (V _{in} Increasing) Low State Output (V _{in} Decreasing) Hysteresis (I _{Sink} = 100 μA)	VIH VIL VH	4.15 4.15 0.02	4.33 4.27 0.09	4.45 4.45 –	V
RESET OUTPUT	•	•			
Output Sink Saturation $ (V_{in} = 4.0 \text{ V, } I_{Sink} = 1.0 \text{ mA}) $ $ (V_{in} = 1.0 \text{ V, } I_{Sink} = 0.25 \text{ mA}) $	VoL	- -	0.14 0.1	0.4 0.3	V
Output Sink Current (Vin, Reset = 4.0 V)	l _{Sink}	7.0	20	50	mA
Output Off-State Leakage (V _{in} , Reset = 5.0 V) (V _{in} , Reset = 10 V)	I _R (leak)	- -	0.02 0.02	0.5 2.0	μА
Clamp Diode Forward Voltage, Pin 1 to 2 (I _F = 5.0 mA)	VF	0.6	0.9	1.2	V
TOTAL DEVICE	•	•		•	
Operating Input Voltage Range	V _{in}	1.0 to 10	-	_	V
Quiescent Input Current V _{in} = 5.0 V V _{in} = 10 V	lin	- -	12 32	20 50	μА

NOTES: 2. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible. $3. T_{low} = 0^{\circ} C$ for MC34164 $T_{high} = +70^{\circ} C$ for MC34164 $= +85^{\circ} C$ for MC33164

Figure 1. MC3X164-3 Reset Output







2.78

2.74

Voltage versus Input Voltage

Figure 3. MC3X164-3 Reset Output

5.0 4.0 V_O, OUTPUT VOLTAGE (V) 3.0 2.0 1.0 $R_L = 82 \text{ k to } V_{in}$ $T_A = 25^{\circ}C$ 2.62

2.66

Figure 4. MC3X164-5 Reset Output Voltage versus Input Voltage 5.0 4.0 V_0 , OUTPUT VOLTAGE (V) 3.0 2.0 1.0 $R_L = 82 \text{ k to } V_{in}$ $T_A = 25^{\circ}C$ 0 4.22 4.26 4.30 4.34 4.38

Figure 5. MC3X164-3 Comparator Threshold **Voltage versus Temperature**

2.70

V_{in}, INPUT VOLTAGE (V)

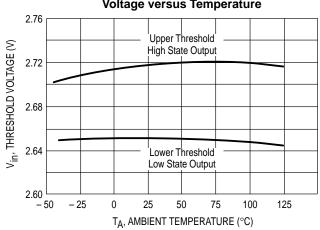


Figure 6. MC3X164-5 Comparator Threshold **Voltage versus Temperature**

V_{in}, INPUT VOLTAGE (V)

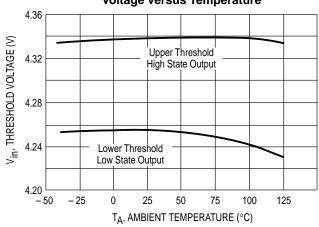


Figure 7. MC3X164-3 Input Current versus Input Voltage

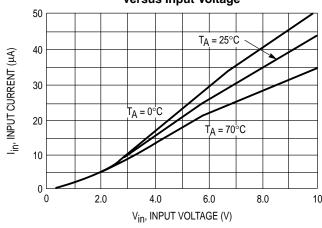


Figure 8. MC3X164-5 Input Current

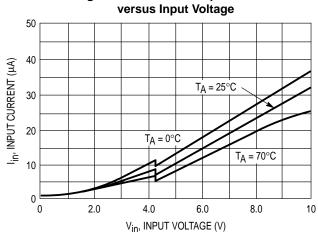


Figure 9. MC3X164–3 Reset Output Saturation versus Sink Current

4.0 $V_{in} = 2.4 \text{ V}$ $T_{A} = 70^{\circ}\text{C}$ $T_{A} = 0^{\circ}\text{C}$ $T_{A} = 70^{\circ}\text{C}$ $T_{A} = 70^{\circ}\text{C}$

8.0

12

V_{Sink}, SINK CURRENT (mA)

16

20

0

0

4.0

Figure 10. MC3X164-5 Reset Output Saturation versus Sink Current 4.0 T_A = 25°C V_{in}, Reset = 4 V V_{OL}, OUTPUT SATURATION (V) $T_A = 70^{\circ}C$ T_A = 0°C 3.0 $T_A = 25^{\circ}C$ 2.0 $T_A = 0^{\circ}C$ 1.0 T_A = 70°C 0 4.0 8.0 20 12 16 ISink, SINK CURRENT (mA)

Figure 11. Clamp Diode Forward Current versus Voltage 32 I F , FORWARD CURRENT (mA) V_{in} = 0 V 24 $T_{A} = 25^{\circ}C$ 16 8.0 0 0 0.4 0.8 1.2 1.6 V_F, FORWARD VOLTAGE (V)

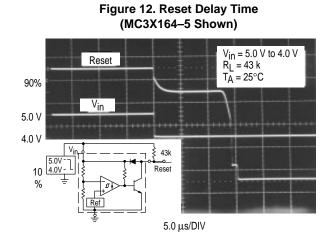
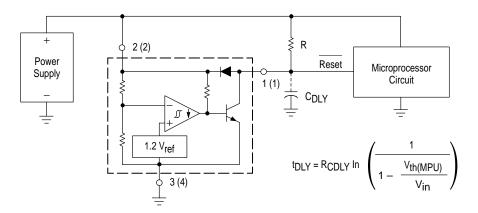
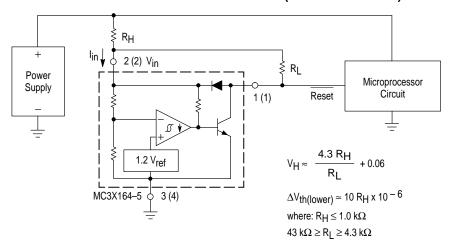


Figure 13. Low Voltage Microprocessor Reset



A time delayed reset can be accomplished with the addition of C_{DLY} . For systems with extremely fast power supply rise times (< 500 ns) it is recommended that the RCDLY time constant be greater than 5.0 μ s. $V_{th(MPU)}$ is the microprocessor reset input threshold.

Figure 14. Low Voltage Microprocessor Reset With Additional Hysteresis (MC3X164–5 Shown)



	Test Data				
V _H (mV)	ΔV _{th} (mV)	R _H (Ω)	R _L (kΩ)		
60	0	0	43		
103	1.0	100	10		
123	1.0	100	6.8		
160	1.0	100	4.3		
155	2.2	220	10		
199	2.2	220	6.8		
280	2.2	220	4.3		
262	4.7	470	10		
306	4.7	470	8.2		
357	4.7	470	6.8		
421	4.7	470	5.6		
530	4.7	470	4.3		

Comparator hysteresis can be increased with the addition of resistor R_H. The hysteresis equation has been simplified and does not account for the change of input current l_{in} as V_{in} crosses the comparator threshold (Figure 8). An increase of the lower threshold $\Delta V_{th}(lower)$ will be observed due to l_{in} which is typically 10 μ A at 4.3 V. The equations are accurate to $\pm 10\%$ with R_H less than 1.0 k Ω and R_L between 4.3 k Ω and 43 k Ω .

Figure 15. Voltage Monitor

Power Supply

1.0 k

1.0 k

1.2 Vref

Figure 16. Solar Powered Battery Charger

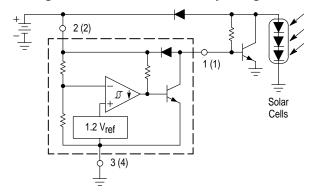
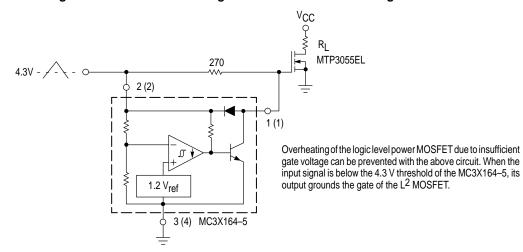
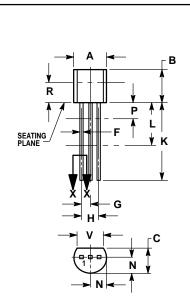


Figure 17. MOSFET Low Voltage Gate Drive Protection Using the MC3X164-5



OUTLINE DIMENSIONS



P SUFFIX PLASTIC PACKAGE CASE 29-04 (TO-226AA) ISSUE AD



- NOTES:

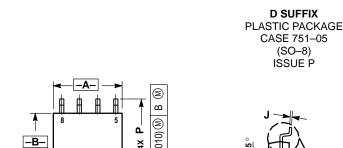
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

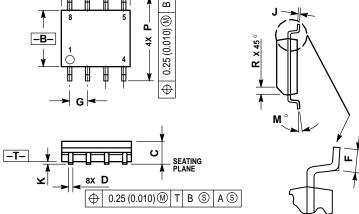
 2. CONTROLLING DIMENSION: INCH.

 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.

 4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION WINIMIMM. IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	





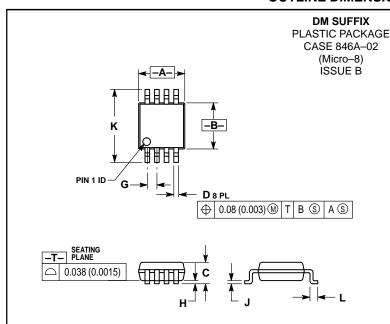
- VOIES.

 1. DIMENSIONS A AND B ARE DATUMS AND T IS A DATUM SURFACE.

 2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 3. DIMENSIONS ARE IN MILLIMETER.
 4. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION D DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	4.80	5.00		
В	3.80	4.00		
С	1.35	1.75		
D	0.35	0.49		
F	0.40	1.25		
G	1.27	1.27 BSC		
J	0.18	0.25		
K	0.10	0.25		
M	0°	7 °		
Р	5.80	6.20		
R	0.25	0.50		

OUTLINE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION D DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION, INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	2.90	3.10	0.114	0.122
С	_	1.10		0.043
D	0.25	0.40	0.010	0.016
G	0.65	BSC	0.026	BSC
Н	0.05	0.15	0.002	0.006
J	0.13	0.23	0.005	0.009
K	4.75	5.05	0.187	0.199
L	0.40	0.70	0.016	0.028

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